



STB141NF55 - STB141NF55-1 STP141NF55

N-channel 55V - 0.0065Ω - 80A - D²PAK - I²PAK - TO-220
STripFET™ II Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)}	I _D ⁽¹⁾
STB141NF55	55V	<0.008Ω	80A
STB141NF55-1	55V	<0.008Ω	80A
STP141NF55	55V	<0.008Ω	80A

1. Current limited by package

Description

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

Applications

- Motor control
- High current, switching application
- Automotive environment

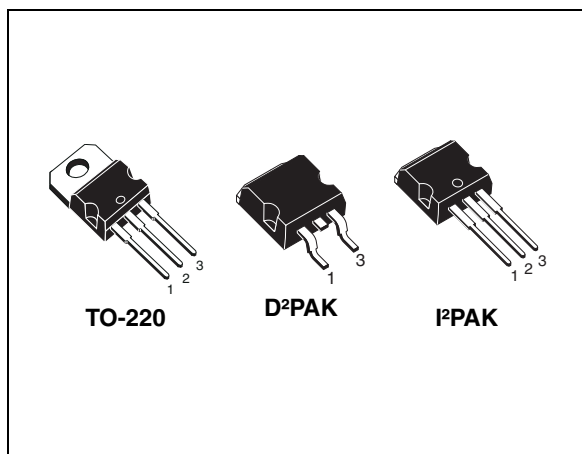


Figure 1. Internal schematic diagram

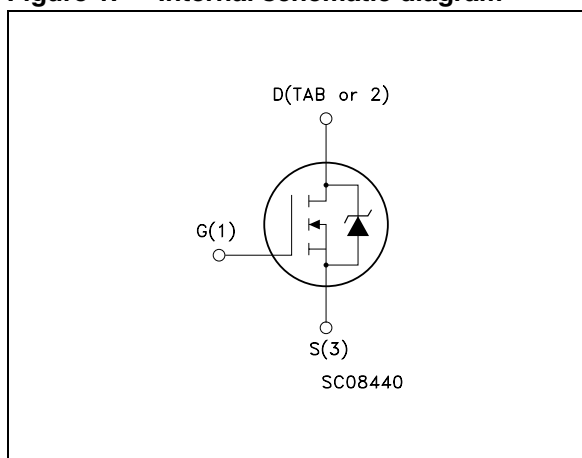


Table 1. Device summary

Order code	Marking	Package	Packaging
STB141NF55	B141NF55	D ² PAK	Tape & reel
STB141NF55-1	B141NF55	I ² PAK	Tube
STP141NF55	P141NF55	TO-220	Tube

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	55	V
V_{GS}	Gate- source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	80	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	80	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	300	W
	Derating factor	2	W/ $^\circ\text{C}$
$dv/dt^{(3)}$	Peak diode recovery voltage slope	10	V/ns
$E_{AS}^{(4)}$	Single pulse avalanche energy	1.3	J
T_{stg}	Storage temperature	-55 to 175	$^\circ\text{C}$
T_j	Operating junction temperature		

1. Current limited by package
2. Pulse width limited by safe operating area
3. $I_{SD} \leq 80\text{A}$, $di/dt \leq 300\text{A}/\mu\text{s}$, $V_{DD} = 80\%V_{(BR)DSS}$
4. Starting $T_j = 25^\circ\text{C}$, $I_D = 40\text{A}$, $V_{DD} = 30\text{V}$

Table 2. Thermal data

Symbol	Parameter	Value		Unit
		TO-220 - I ² PAK	D ² PAK	
$R_{thj-case}$	Thermal resistance junction-case max	0.5		$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	--	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	--	35	$^\circ\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose (for 10 sec, 1.6mm from case)	300		$^\circ\text{C}$

1. When mounted on 1 inch², FR4 board, 2 oz Cu

2 Electrical characteristics

($T_{CASE} = 25^{\circ}\text{C}$ unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0$	55			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$, $T_C = 125^{\circ}\text{C}$			1 10	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\ \text{V}$, $I_D = 40\ \text{A}$		0.0065	0.008	Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\text{V}$, $I_D = 40\ \text{A}$		100		S
C_{iss}	Input capacitance	$V_{DS} = 25\text{V}$, $f = 1\ \text{MHz}$ $V_{GS} = 0$		5300		pF
C_{oss}	Output capacitance			1000		pF
C_{rss}	Reverse transfer capacitance			290		pF
Q_g	Total gate charge	$V_{DD} = 44\text{V}$, $I_D = 80\text{A}$		142		nC
Q_{gs}	Gate-source charge	$V_{GS} = 10\text{V}$		27		nC
Q_{gd}	Gate-drain charge	(see Figure 14)		55		nC

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	$V_{DD} = 27.5\text{ V}$, $I_D = 40\text{ A}$ $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 13)		30 150		ns ns
$t_{d(off)}$ t_f	Turn-off-delay time Fall time	$V_{DD} = 27.5\text{ V}$, $I_D = 40\text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 13)		125 45		ns ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)				80 320	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 80\text{ A}$, $V_{GS} = 0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 80\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 20\text{ V}$, $T_j = 150^\circ\text{C}$ (see Figure 15)		90 275 6.5		ns nC A

1. Pulse width limited safe operating area

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

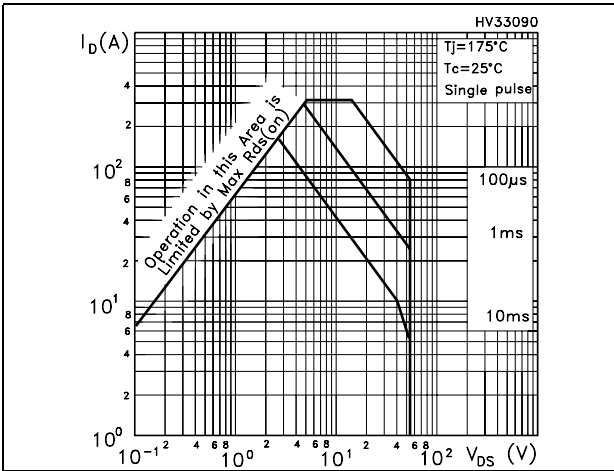


Figure 2. Thermal impedance

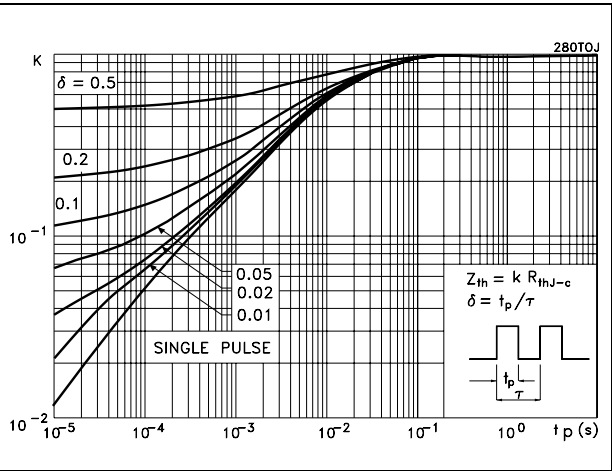


Figure 3. Output characteristics

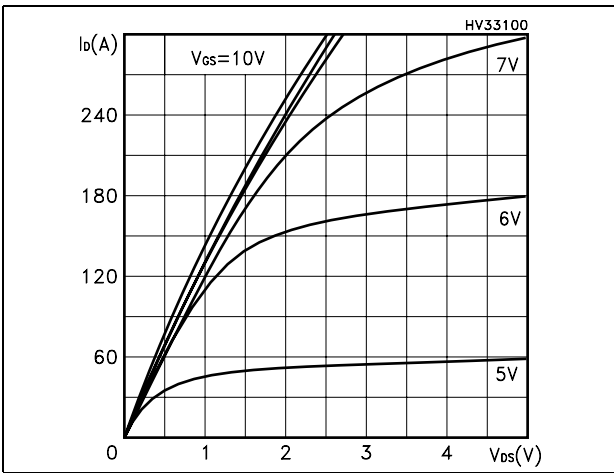


Figure 4. Transfer characteristics

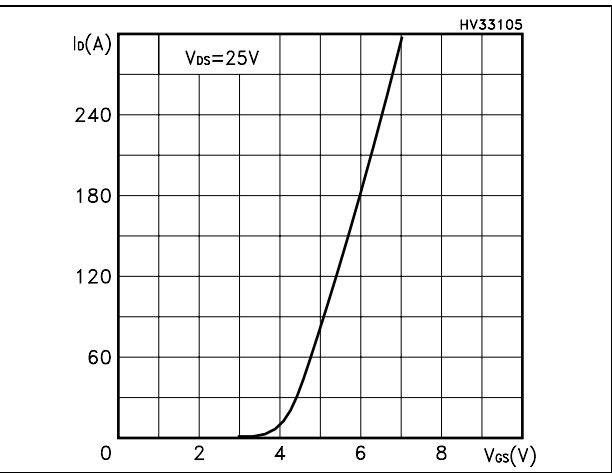


Figure 5. Transconductance

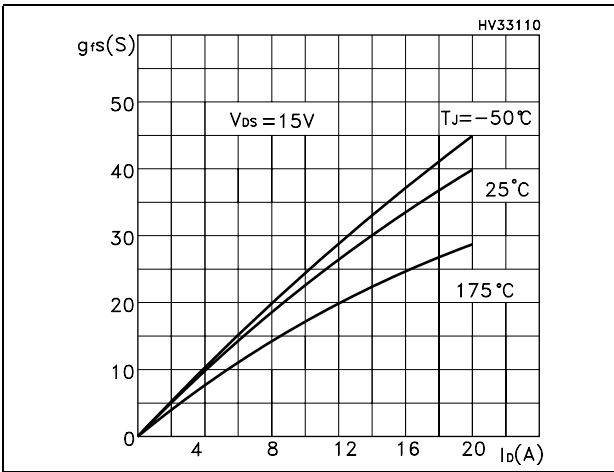


Figure 6. Static drain-source on resistance

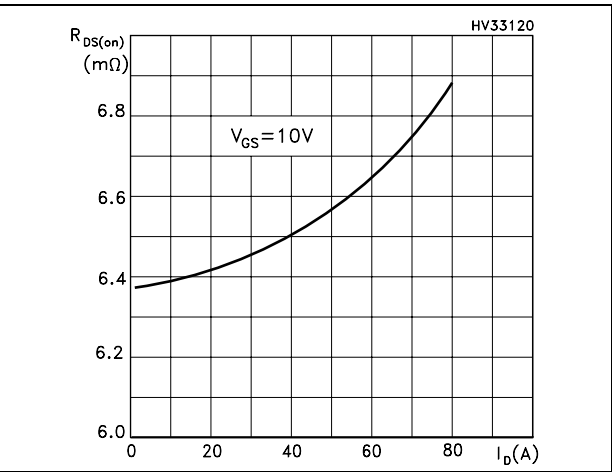


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

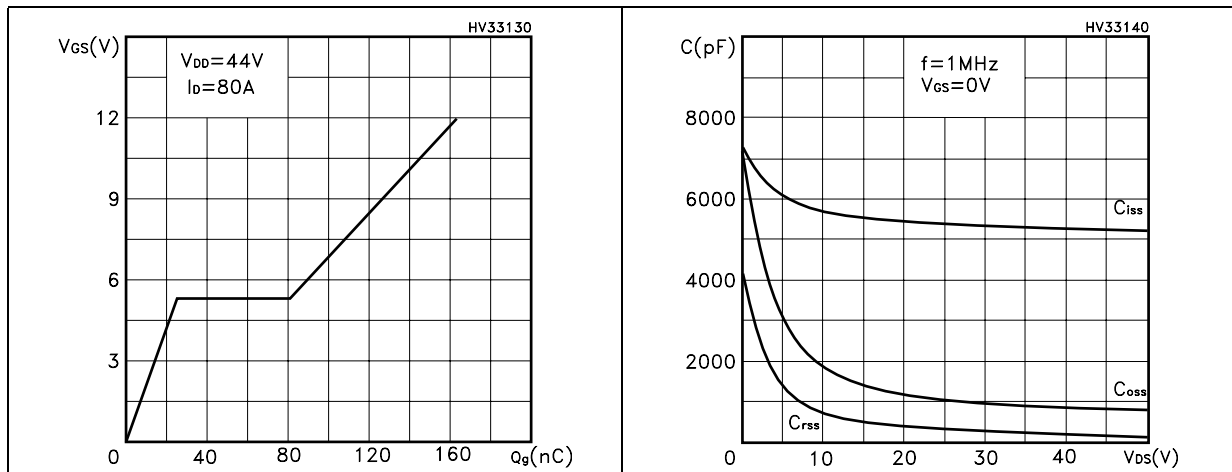


Figure 9. Normalized gate threshold voltage vs temperature

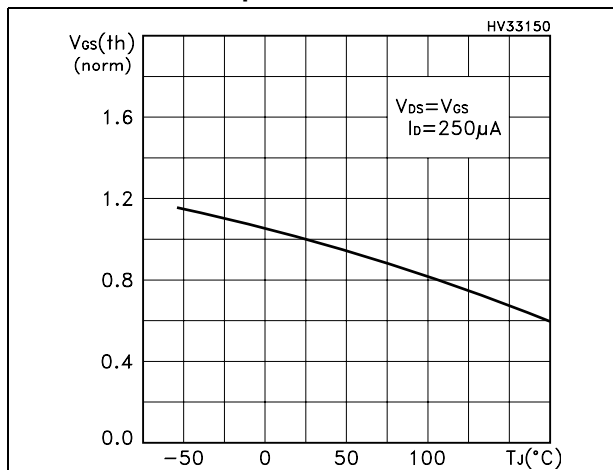


Figure 10. Normalized on resistance vs temperature

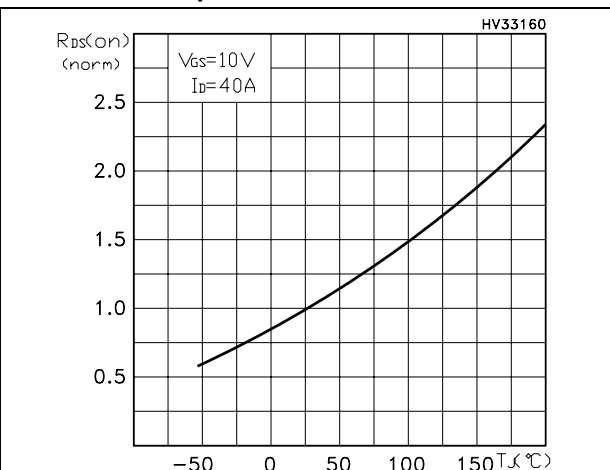
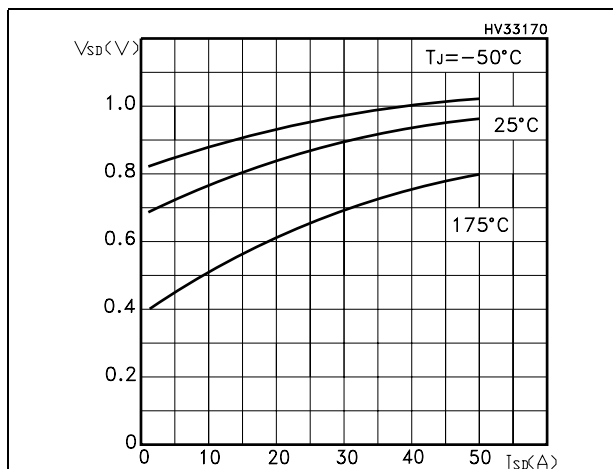
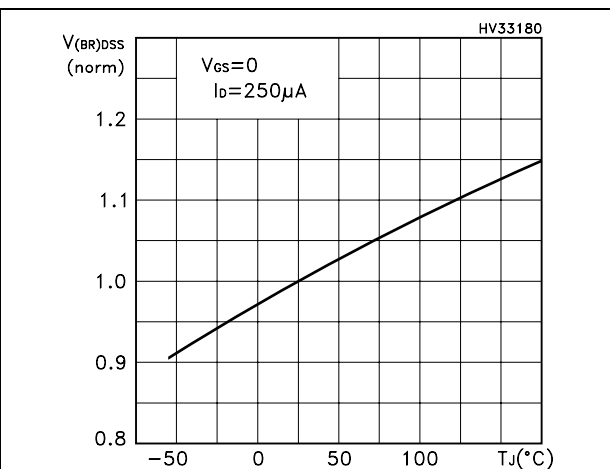


Figure 11. Source-drain diode forward characteristics

Figure 12. Normalized $B_{V_{DS}}$ vs temperature

3 Test circuit

Figure 13. Switching times test circuit for resistive load

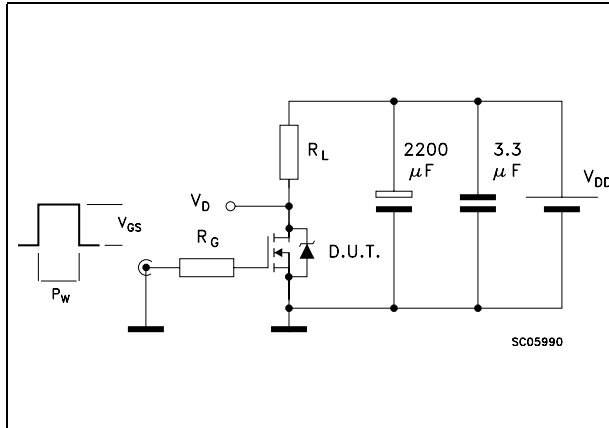


Figure 14. Gate charge test circuit

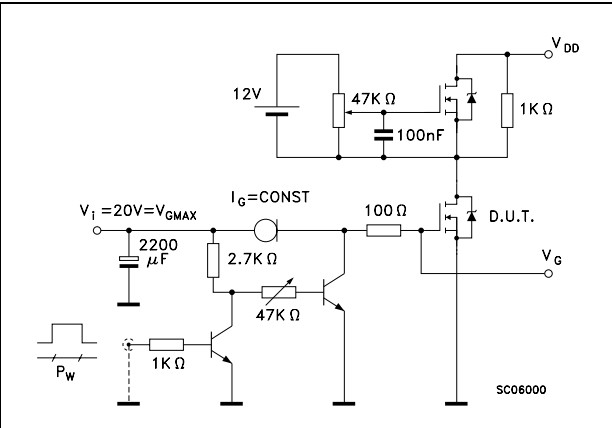


Figure 15. Test circuit for inductive load switching and diode recovery times

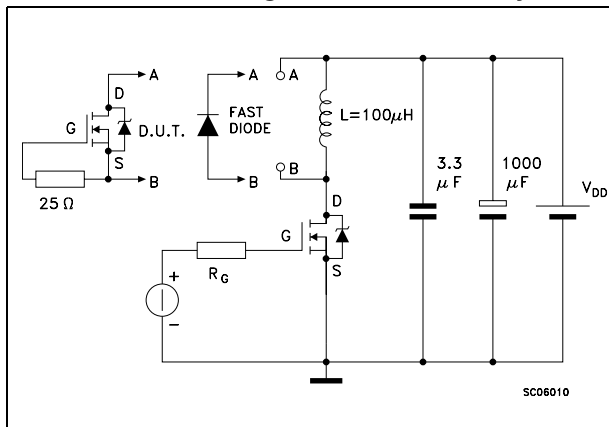


Figure 16. Unclamped inductive load test circuit

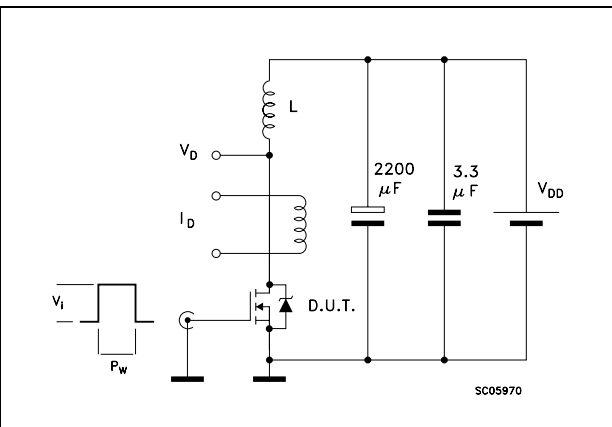


Figure 17. Unclamped inductive waveform

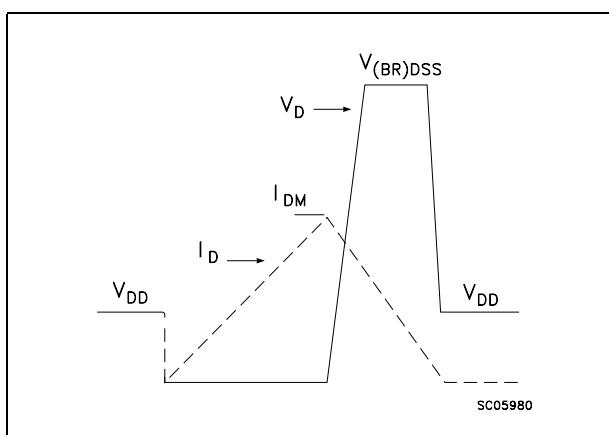
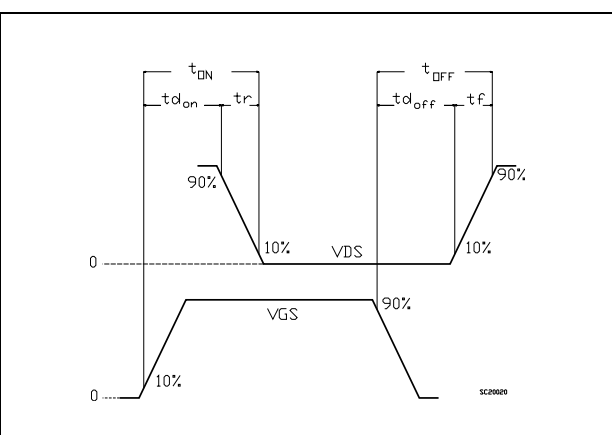


Figure 18. Switching time waveform

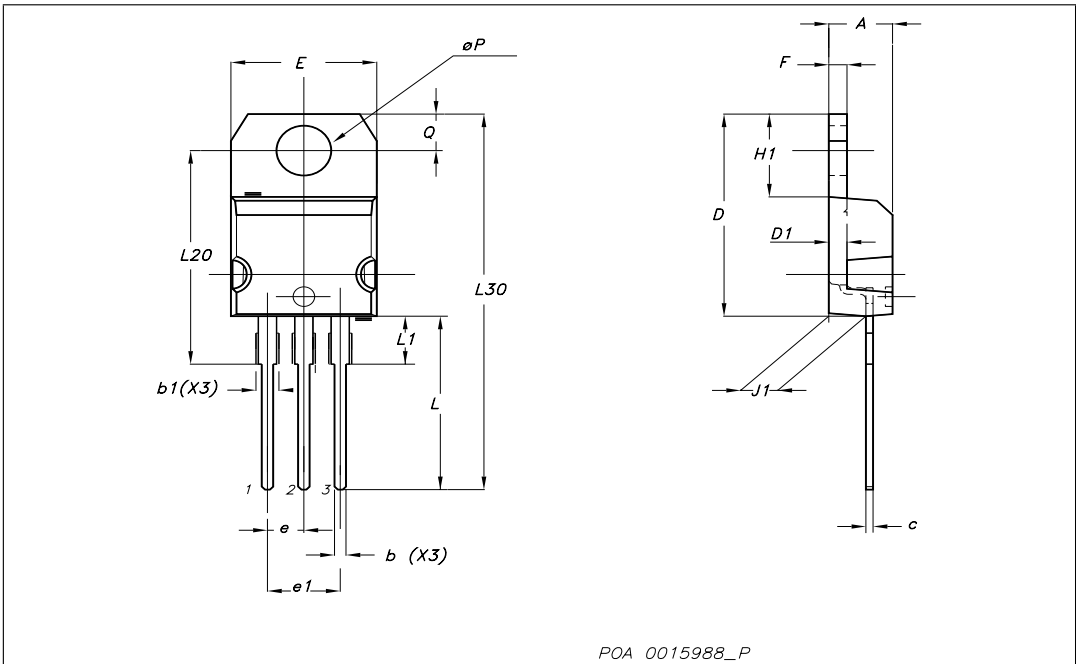


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

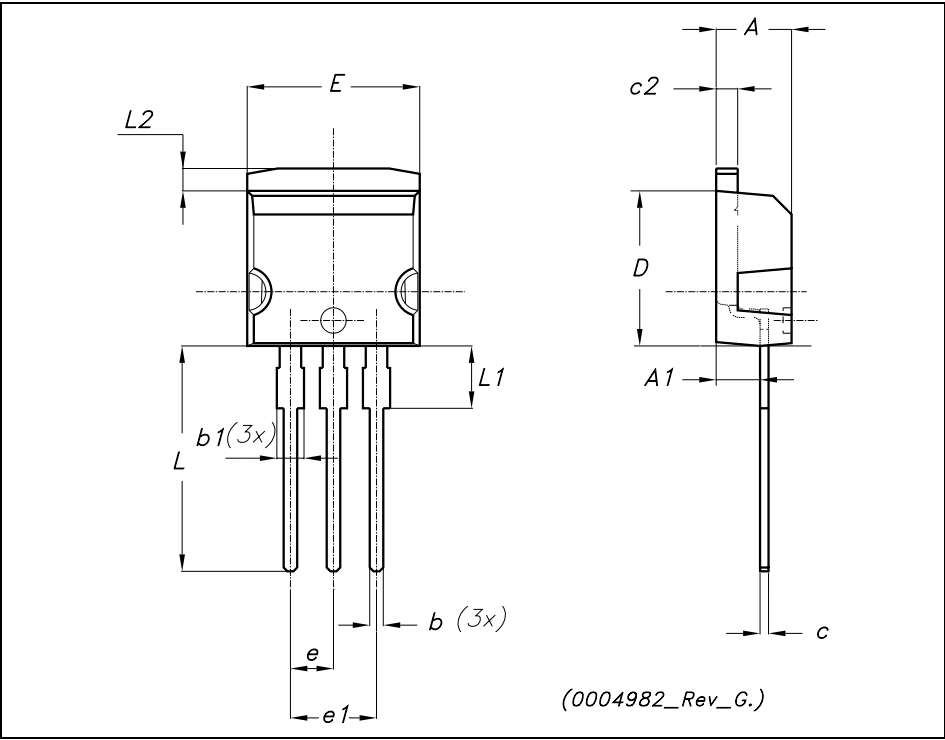
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
θP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



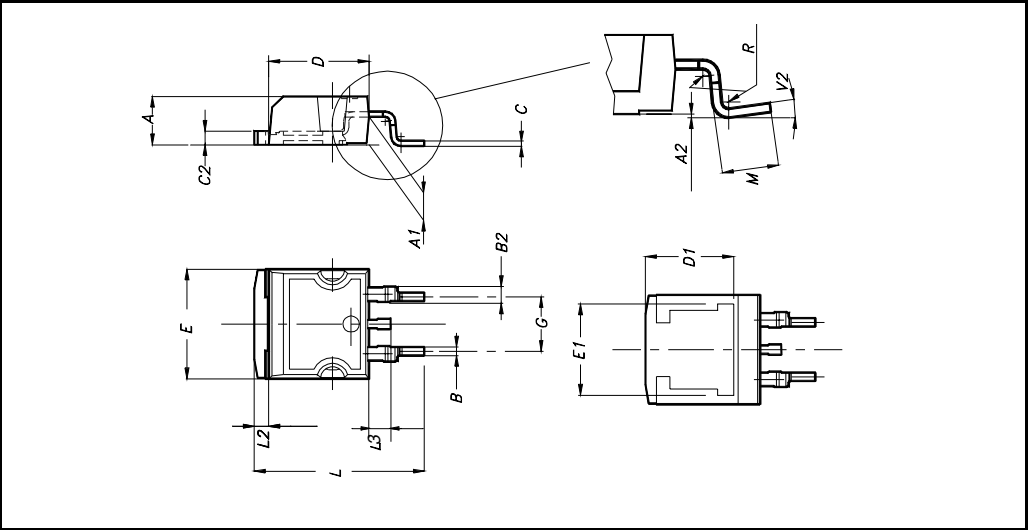
TO-262 (I²PAK) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



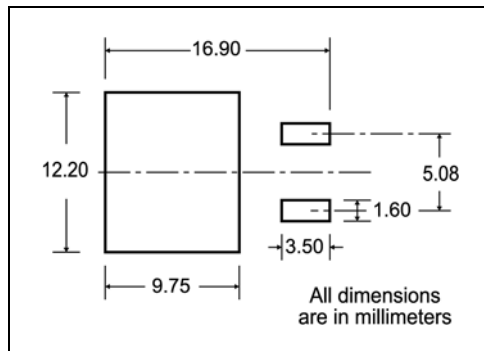
D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			

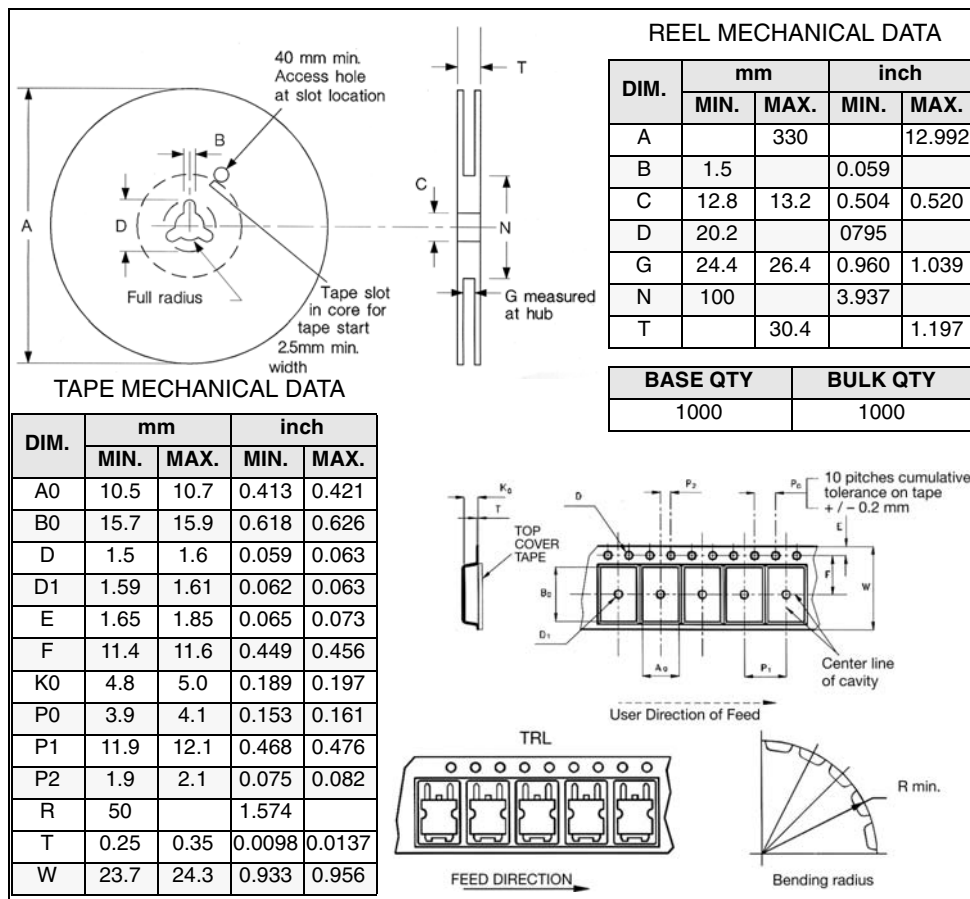


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 7. Document revision history

Date	Revision	Changes
01-Aug-2007	1	Initial release.

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